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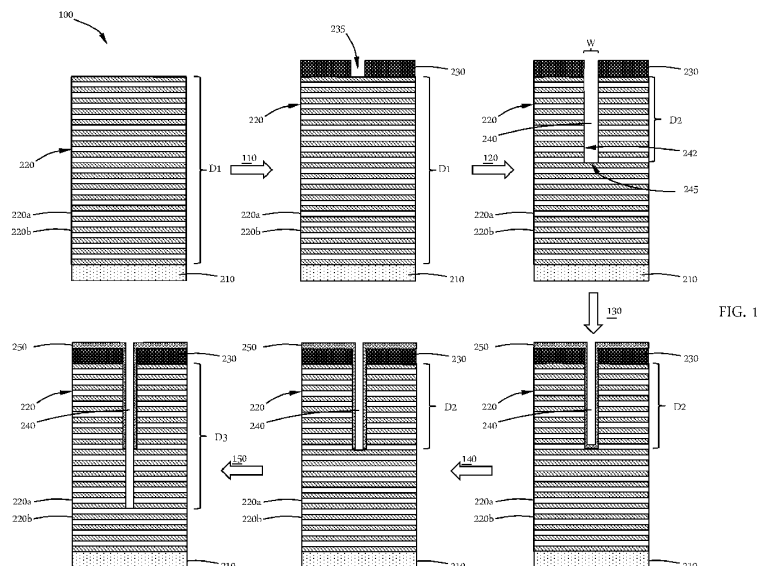


FIG. 1

(57) Abstract: Methods of etching film stacks to form gaps of uniform width are described. A film stack is etched through a hardmask. A conformal liner is deposited in the gap. The bottom of the liner is removed. The film stack is selectively etched relative to the liner. The liner is removed. The method may be repeated to a predetermined depth.

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